74ABT126

Quad buffer; 3-state

Rev. 04 — 17 February 2005 Product data sheet

1. General description

The 74ABT126 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT126 device is a quad buffer that is ideal for driving bus lines. The device features four output enable inputs (nOE each controlling one of the 3-state outputs (nY).

2. Features

- Quad bus interface
- 3-state buffers
- Live insertion and extraction permitted
- Output capability: +64 mA and –32 mA
- Inputs are disabled during 3-state mode
- Power-up 3-state
- Latch-up protection:
  - JESD78: exceeds 500 mA
- ESD protection:
  - MIL STD 883 method 3015: exceeds 2000 V
  - Machine model: exceeds 200 V

3. Quick reference data

Table 1: Quick reference data

T_{amb} = 25 °C; GND = 0 V.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PLH}	propagation delay nA to nY	C_L = 50 pF; V_{CC} = 5 V	-	2.9	-	ns
t_{PHL}	propagation delay nA to nY	C_L = 50 pF; V_{CC} = 5 V	-	3.0	-	ns
C_I	input capacitance	V_I = 0 V or V_{CC}	-	4	-	pF
C_O	output capacitance	outputs disabled; V_O = 0 V or V_{CC}	-	7	-	pF
I_{CC}	quiescent supply current	outputs 3-state; V_{CC} = 5.5 V	-	65	-	µA

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4. Ordering information

Table 2: Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74ABT126D	–40 °C to +85 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74ABT126DB	–40 °C to +85 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74ABT126PW	–40 °C to +85 °C	TSSOP14	plastic thin small outline package; 14 leads; body width 4.4 mm	SOT402-1

5. Functional diagram

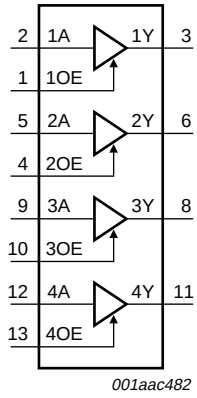


Fig 1. Logic symbol

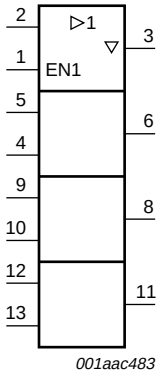


Fig 2. IEC logic symbol

6. Pinning information

6.1 Pinning

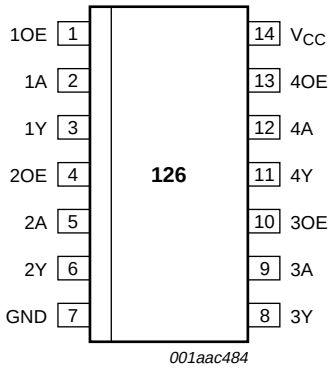


Fig 3. Pin configuration

6.2 Pin description

Table 3: Pin description

Symbol	Pin	Description
1OE	1	1 output enable input
1A	2	1 data input
1Y	3	1 data output
2OE	4	2 output enable input
2A	5	2 data input
2Y	6	2 data output
GND	7	ground (0 V)
3Y	8	3 data output
3A	9	3 data input
3OE	10	3 output enable input
4Y	11	4 data output
4A	12	4 data input
4OE	13	4 output enable input
V_{CC}	14	supply voltage

7. Functional description

7.1 Function table

Table 4: Function table [1]

Input		Output
nOE	nA	nY
H	L	L
H	H	H
L	X	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

8. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
V_I	input voltage		[1]	–1.2	+7.0	V
V_O	output voltage	output in OFF-state or HIGH-state	[1]	–0.5	+5.5	V
I_{IK}	input diode current	$V_I < 0$ V		-	–18	mA
I_{OK}	output diode current	$V_O < 0$ V		-	–50	mA
I_O	output current	output in LOW-state		-	128	mA
T_j	junction temperature		[2]	-	150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

9. Recommended operating conditions

Table 6: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		4.5	-	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V_{IL}	LOW-level input voltage		-	-	0.8	V
I_{OH}	HIGH-level output current		-	-	–32	mA
I_{OL}	LOW-level output current		-	-	64	mA
$\Delta t/\Delta V$	input transition rise or fall rate		0	-	10	ns/V
T_{amb}	ambient temperature	in free air	–40	-	+85	°C

10. Static characteristics

Table 7: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = 25 °C							
V_{IK}	input clamp voltage	V_{CC} = 4.5 V; I_{IK} = –18 mA		-	–0.9	–1.2	V
V_{OH}	HIGH-level output voltage	V_{CC} = 4.5 V; V_I = V_{IL} or V_{IH}					
		I_{OH} = –3 mA		2.5	2.9	-	V
		I_{OH} = –32 mA		2.0	2.4	-	V
		V_{CC} = 5.0 V; V_I = V_{IL} or V_{IH}					
		I_{OH} = –3 mA		3.0	3.4	-	V
V_{OL}	LOW-level output voltage	V_{CC} = 4.5 V; V_I = V_{IL} or V_{IH}					
		I_{OL} = 64mA		-	0.35	0.55	V
I_{LI}	input leakage current	V_{CC} = 5.5 V; V_I = GND or 5.5 V		-	±0.01	±1.0	µA
I_{OFF}	power-off leakage current	V_{CC} = 0 V; V_O or V_I ≤ 4.5 V		-	±5.0	±100	µA
I_{PU}, I_{PD}	power-up or power-down down 3-state output current	V_{CC} = 2.1 V; V_O = 0.5 V; V_I = GND or V_{CC}; V_{OE} = don't care	[1]	-	±5.0	±50	µA
I_{OZ}	3-state output current	V_{CC} = 5.5 V; V_I = V_{IL} or V_{IH}					
		output HIGH-state at V_O = 2.7 V		-	1.0	50	µA
		output LOW-state at V_O = 0.5 V		-	–1.0	–50	µA
I_{CEX}	output HIGH-state leakage current	V_{CC} = 5.5 V; V_O = 5.5 V; V_I = GND or V_{CC}		-	5.0	50	µA
I_O	output current	V_{CC} = 5.5 V; V_O = 2.5 V	[2]	–50	–100	–180	mA
I_{CC}	quiescent supply current	V_{CC} = 5.5 V; V_I = GND or V_{CC}					
		outputs HIGH-state		-	65	250	µA
		outputs LOW-state		-	12	15	mA
		outputs 3-state		-	65	250	µA
ΔI_{CC}	additional supply current						
	per data input pin	one data input at 3.4 V and other inputs at V_{CC} or GND; V_{CC} = 5.5 V	[3]				
		outputs enabled		-	0.5	1.5	mA
		outputs 3-state		-	50	250	µA
	per enable input pin	one enable input at 3.4 V and other inputs at V_{CC} or GND; V_{CC} = 5.5 V	[3]				
		outputs 3-state		-	0.5	1.5	mA
C_I	input capacitance	V_I = 0 V or V_{CC}		-	4	-	pF
C_O	output capacitance	outputs disabled; V_O = 0 V or V_{CC}		-	7	-	pF
T_{amb} = –40 °C to +85 °C							
V_{IK}	input clamp voltage	V_{CC} = 4.5 V; I_{IK} = –18 mA		-	-	–1.2	V

Table 7: Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{OH}	HIGH-level output voltage	V_{CC} = 4.5 V; V_I = V_{IL} or V_{IH}					
		I_{OH} = –3 mA		2.5	-	-	V
		I_{OH} = –32 mA		2.0	-	-	V
		V_{CC} = 5.0 V; V_I = V_{IL} or V_{IH}					
		I_{OH} = –3 mA		3.0	-	-	V
V_{OL}	LOW-level output voltage	V_{CC} = 4.5 V; V_I = V_{IL} or V_{IH}					
		I_{OL} = 64 mA		-	-	0.55	V
I_{LI}	input leakage current	V_{CC} = 5.5 V; V_I = GND or 5.5 V		-	-	±1.0	µA
I_{OFF}	power-off leakage current	V_{CC} = 0.0 V; V_O or $V_I \leq$ 4.5 V		-	-	±100	µA
I_{PU}, I_{PD}	power-up or power-down down 3-state output current	V_{CC} = 2.1 V; V_O = 0.5 V; V_I = GND or V_{CC}; V_{nOE} = don't care	[1]	-	-	±50	µA
I_{OZ}	3-state output current	V_{CC} = 5.5 V; V_I = V_{IL} or V_{IH}					
		output HIGH-state at V_O = 2.7 V		-	-	50	µA
		output LOW-state at V_O = 0.5 V		-	-	–50	µA
I_{CEX}	output HIGH-state leakage current	V_{CC} = 5.5 V; V_O = 5.5 V; V_I = GND or V_{CC}		-	-	50	µA
I_O	output current	V_{CC} = 5.5 V; V_O = 2.5 V	[2]	–50	-	–180	mA
I_{CC}	quiescent supply current	V_{CC} = 5.5 V; V_I = GND or V_{CC}					
		outputs HIGH-state		-	-	250	µA
		outputs LOW-state		-	-	15	mA
		outputs 3-state		-	-	250	µA
ΔI_{CC}	additional supply current						
	per data input pin	one data input at 3.4 V and other inputs at V_{CC} or GND; V_{CC} = 5.5 V	[3]				
		outputs enabled		-	-	1.5	mA
		outputs 3-state		-	-	250	µA
	per enable input pin	one enable input at 3.4 V and other inputs at V_{CC} or GND; V_{CC} = 5.5 V	[3]				
		outputs 3-state		-	-	1.5	mA

[1] This parameter is valid for any V_{CC} between 0 V and 2.1 V, with a transition time of up to 10 ms. From V_{CC} = 2.1 V to V_{CC} = 5 V ± 10 % a transition time of up to 100 µs is permitted.

[2] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

[3] This is the increase in supply current for each input at 3.4 V.

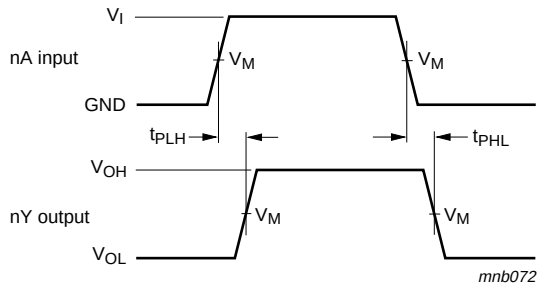
11. Dynamic characteristics

Table 8: Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C; V_{CC} = 5.0 V						
t_{PLH}	propagation delay nA to nY	see Figure 4	1.0	2.9	4.2	ns
t_{PHL}	propagation delay nA to nY	see Figure 4	1.0	3.0	4.3	ns
t_{PZH}	output enable time to HIGH-level	see Figure 5	1.5	3.2	5.8	ns
t_{PZL}	output enable time to LOW-level	see Figure 5	1.9	4.4	5.9	ns
t_{PHZ}	output disable time from HIGH-level	see Figure 5	1.0	4.2	5.2	ns
t_{PLZ}	output disable time from LOW-level	see Figure 5	1.0	2.9	4.9	ns
T_{amb} = −40 °C to +85 °C; V_{CC} = 5.0 V ± 0.5 V						
t_{PLH}	propagation delay nA to nY	see Figure 4	1.0	-	4.4	ns
t_{PHL}	propagation delay nA to nY	see Figure 4	1.0	-	4.6	ns
t_{PZH}	output enable time to HIGH-level	see Figure 5	1.5	-	6.5	ns
t_{PZL}	output enable time to LOW-level	see Figure 5	1.9	-	6.5	ns
t_{PHZ}	output disable time from HIGH-level	see Figure 5	1.0	-	5.8	ns
t_{PLZ}	output disable time from LOW-level	see Figure 5	1.0	-	5.5	ns

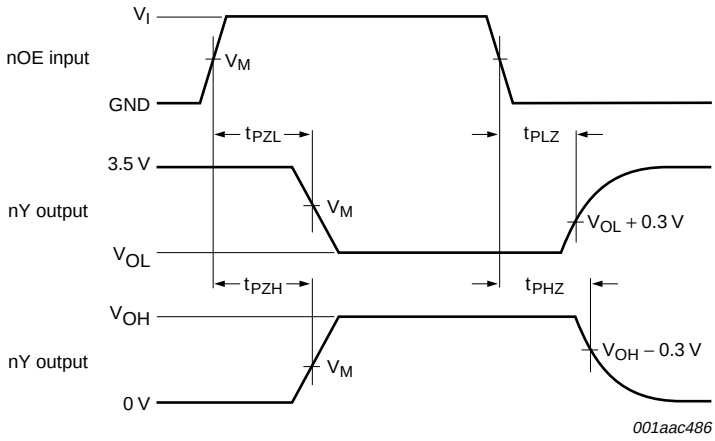
12. Waveforms



V_M = 1.5 V.

V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

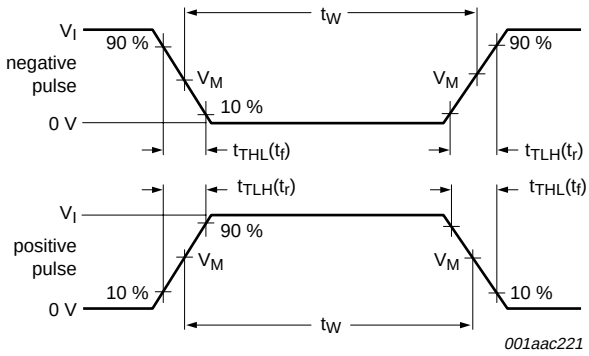
Fig 4. Propagation delay input (nA) to output (nY)



V_M = 1.5 V.

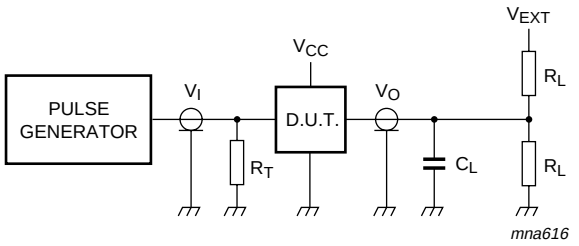
V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

Fig 5. Enable and disable times of 3-state outputs



V_M = 1.5 V.

a. Input pulse definition



Test data is given in Table 9.

Definitions test circuit:

R_L = Load resistor.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = Test voltage for switching times.

b. Test circuit

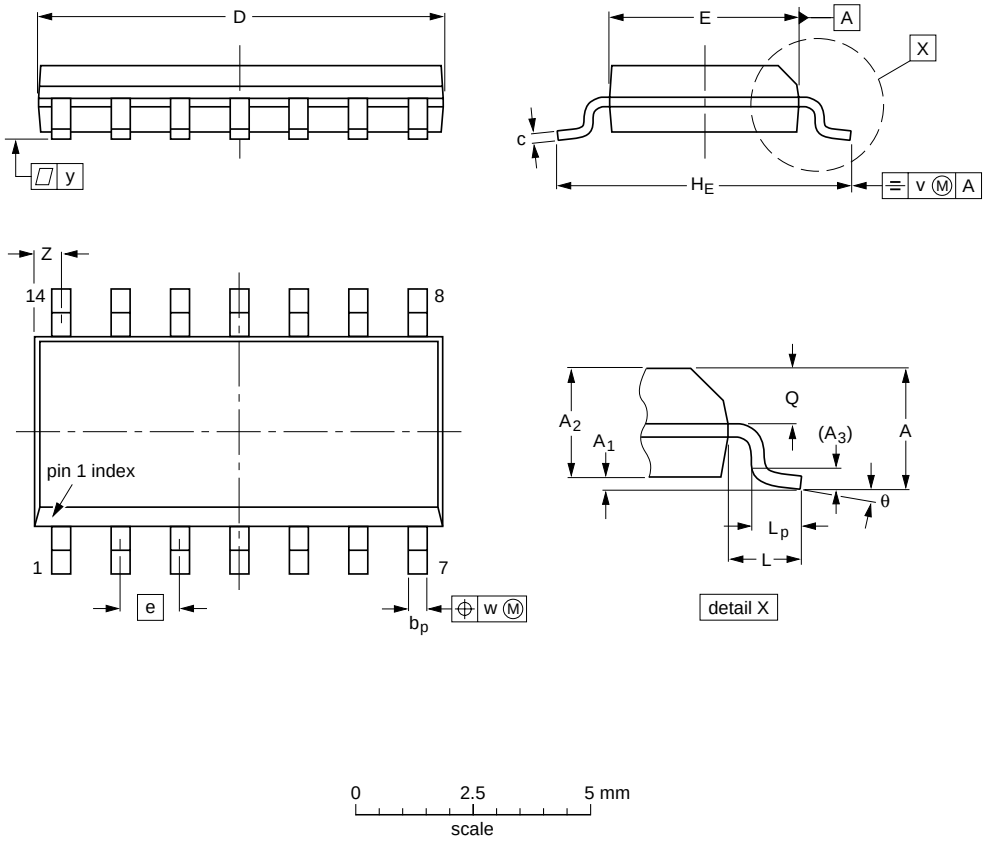
Fig 6. Load circuitry for switching times

Table 9: Test data

Input				Load		V_{EXT}		
V_I	f_i	t_W	t_r, t_f	C_L	R_L	t_{PHZ}, t_{PZH}	t_{PLZ}, t_{PZL}	t_{PLH}, t_{PHL}
3.0 V	≤ 1 MHz	500 ns	≤ 2.5 ns	50 pF	500 Ω	open	7.0 V	open

13. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

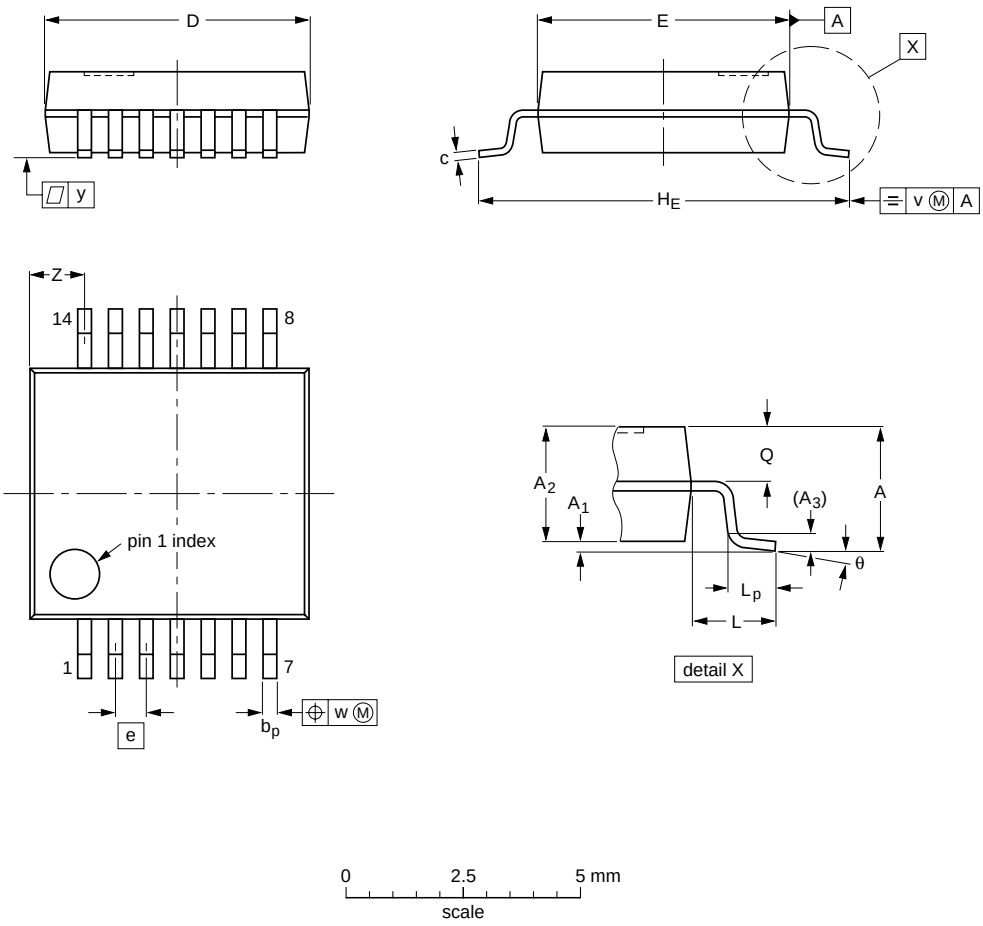
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 7. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm **SOT337-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8^o 0^o

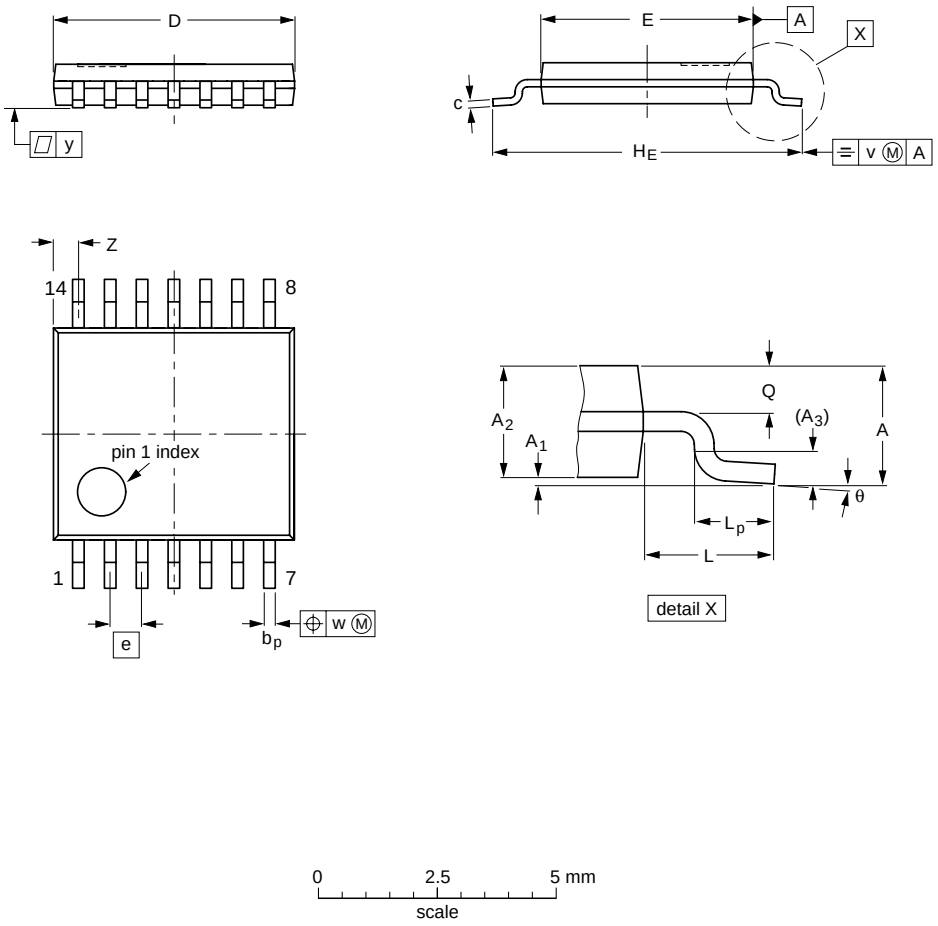
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT337-1		MO-150				~~99-12-27~~ 03-02-19

Fig 8. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm **SOT402-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT402-1		MO-153				~~99-12-27~~ 03-02-18

Fig 9. Package outline SOT402-1 (TSSOP14)

14. Revision history

Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74ABT126_4	20050217	Product data sheet	-	9397 750 14597	74ABT126_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors. • Section 2 “Features”: modified ‘JEDEC Std 17’ into ‘JESD78’. • Table 8 “Dynamic characteristics”: changed min value of t_{PZH} from 1.9 ns into 1.5 ns for both conditions V_{CC} = 5.0 V at T_{amb} = 25 °C and V_{CC} = 5.0 V ± 0.5 V at T_{amb} = –40 °C to +85 °C.				
74ABT126_3	20021213	Product specification	-	9397 750 10856	74ABT126_2
74ABT126_2	19980116	Product specification	-	9397 750 03462	74ABT126_1
74ABT126_1	-	-	-	-	-

15. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

16. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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19. Contents

Date of release: 17 February 2005
Document number: 9397 750 14597

Published in The Netherlands